

# Enhanced performance of $\text{Sb}_2\text{S}_3$ mesoscopic sensitized solar cells employing $\text{TiO}_2\text{:Nb}$ compact layer

## Abstract:

This paper reports on the enhancement of charge transport and recombination by niobium doped compact layers of  $\text{TiO}_2$  in a solar cell with  $\text{Sb}_2\text{S}_3$  absorber layer by characterizing both thin films of  $\text{TiO}_2\text{:Nb}$  and working solar cell devices with the layer stack FTO/cp- $\text{TiO}_2\text{:Nb}$ /mp- $\text{TiO}_2$ / $\text{Sb}_2\text{S}_3$ /P3HT/ $\text{MoO}_x$ /Ag. The electron transport layers of  $\text{TiO}_2$  doped with 0.14 and 0.27 at.% Nb were prepared by spin coating and have no structural change as determined from the analysis of GIXRD spectra. SEM images show thin pin hole free layers of the cp- $\text{TiO}_2\text{:Nb}$  on FTO crystals that are agglomerates of particles. Analysis of the current–voltage curves of the solar cells with  $\text{Sb}_2\text{S}_3$  as the absorber material showed increased short-circuit current, fill factor and power conversion efficiency from 1.3 to 1.7%. The enhancement of the device performance is attributed to substitution of Ti ions with Nb ions in the  $\text{TiO}_2$  resulting in a change in the band alignment of the solar cells with Nb content. This results in increase in charge recombination resistance in the  $\text{Sb}_2\text{S}_3$  layer as determined from the analysis of the impedance spectroscopy measurements.

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